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TRANSMITTAL FORM

(to be used for all correspondence after initial filing)

		Application No.	10/691,852
		Filing Date	October 22, 2003
		First Named Inventor	Tae Woong Kang
		Art Unit	
		Examiner Name	
Total Number of Pages in This Submission	9	Attorney Docket Number	5882P061

ENCLOSURES (check all that apply)

<input checked="" type="checkbox"/> Fee Transmittal Form <input type="checkbox"/> Fee Attached <input type="checkbox"/> Amendment / Response <input type="checkbox"/> After Final <input type="checkbox"/> Affidavits/declaration(s) <input type="checkbox"/> Extension of Time Request <input type="checkbox"/> Express Abandonment Request <input checked="" type="checkbox"/> Information Disclosure Statement <input checked="" type="checkbox"/> PTO/SB/08 <input type="checkbox"/> Certified Copy of Priority Document(s) <input type="checkbox"/> Response to Missing Parts/Incomplete Application <input type="checkbox"/> Basic Filing Fee <input type="checkbox"/> Declaration/POA <input type="checkbox"/> Response to Missing Parts under 37 CFR 1.52 or 1.53	<input type="checkbox"/> Drawing(s) <input type="checkbox"/> Licensing-related Papers <input type="checkbox"/> Petition <input type="checkbox"/> Petition to Convert a Provisional Application <input type="checkbox"/> Power of Attorney, Revocation Change of Correspondence Address <input type="checkbox"/> Terminal Disclaimer <input type="checkbox"/> Request for Refund <input type="checkbox"/> CD, Number of CD(s)	<input type="checkbox"/> After Allowance Communication to Group <input type="checkbox"/> Appeal Communication to Board of Appeals and Interferences <input type="checkbox"/> Appeal Communication to Group (Appeal Notice, Brief, Reply Brief) <input type="checkbox"/> Proprietary Information <input type="checkbox"/> Status Letter <input checked="" type="checkbox"/> Other Enclosure(s) (please identify below): <div style="border: 1px solid black; padding: 5px; margin-top: 5px;"> Korean Office Action; Prior Art Reference (1); return postcard </div>
Remarks		

SIGNATURE OF APPLICANT, ATTORNEY, OR AGENT

Firm or Individual name	Eric S. Hyman, Reg. No. 30,139 BLAKELY, SOKOLOFF, TAYLOR & ZAFMAN LLP
Signature	
Date	8/1/04

CERTIFICATE OF MAILING/TRANSMISSION

I hereby certify that this correspondence is being deposited with the United States Postal Service on the date shown below with sufficient postage as first class mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

Typed or printed name	Melissa Stead		
Signature		Date	8-11-04



FEE TRANSMITTAL for FY 2004

Effective 01/01/2004. Patent fees are subject to annual revision.

Complete if Known

Application Number	10/691,852
Filing Date	October 22, 2003
First Named Inventor	Tae Woong Kang
Examiner Name	
Art Unit	
Attorney Docket No.	5882P061

☒ Applicant claims small entity status. See 37 CFR 1.27.

TOTAL AMOUNT OF PAYMENT (\$)

METHOD OF PAYMENT (check all that apply)

☐ Check ☐ Credit card ☐ Money Order ☐ Other ☐ None

☒ Deposit Account

Deposit
Account
Number

02-2666

Deposit
Account
Name

Blakely, Sokoloff, Taylor & Zafman LLP

The Commissioner is authorized to: (check all that apply)

☒ Charge fee(s) indicated below

☐ Credit any overpayments

☒ Charge any additional fee(s) or underpayment of fees as required under 37 CFR §§ 1.16, 1.17, 1.18 and 1.20.

☐ Charge fee(s) indicated below, except for the filing fee to the above-identified deposit account

FEE CALCULATION

1. BASIC FILING FEE

Large Entity		Small Entity		Fee Description	Fee Paid
Fee Code	Fee (\$)	Fee Code	Fee (\$)		
1001	770	2001	385	Utility filing fee	
1002	340	2002	170	Design filing fee	
1003	530	2003	265	Plant filing fee	
1004	770	2004	385	Reissue filing fee	
1005	160	2005	80	Provisional filing fee	
SUBTOTAL (1)					

2. EXTRA CLAIM FEES

Total Claims - 20** = X =

Independent Claims - 3 = X =

Multiple Dependent =

Large Entity		Small Entity		Fee Description	Fee Paid
Fee Code	Fee (\$)	Fee Code	Fee (\$)		
1202	18	2202	9	Claims in excess of 20	
1201	86	2201	43	Independent claims in excess of 3	
1203	290	2203	145	Multiple Dependent claim, if not paid	
1204	86	2204	43	**Reissue independent claims over original patent	
1205	18	2205	9	**Reissue claims in excess of 20 and over original patent	
SUBTOTAL (2)					

**or number previously paid, if greater, For Reissues, see below

FEE CALCULATION (continued)

3. ADDITIONAL FEES

Large Entity		Small Entity		Fee Description	Fee Paid
Fee Code	Fee (\$)	Fee Code	Fee (\$)		
1051	130	2051	65	Surcharge - late filing fee or oath	
1052	50	2052	25	Surcharge - late provisional filing fee or cover sheet	
2053	130	2053	130	Non-English specification	
1812	2,520	1812	2,520	For filing a request for ex parte reexamination	
1804	920 *	1804	920 *	Requesting publication of SIR prior to Examiner action	
1805	1,840 *	1805	1,840 *	Requesting publication of SIR after Examiner action	
1251	110	2251	55	Extension for reply within first month	
1252	420	2252	210	Extension for reply within second month	
1253	960	2253	475	Extension for reply within third month	
1254	1,480	2254	740	Extension for reply within fourth month	
1255	2,010	2255	1,005	Extension for reply within fifth month	
1404	330	2401	165	Notice of Appeal	
1402	330	2402	165	Filing a brief in support of an appeal	
1403	280	2403	145	Request for oral hearing	
1451	1,510	2451	1,510	Petition to institute a public use proceeding	
1452	110	2452	55	Petition to revive - unavoidable	
1453	1,330	2453	665	Petition to revive - unintentional	
1501	1,330	2501	665	Utility issue fee (or reissue)	
1502	480	2502	240	Design issue fee	
1503	640	2503	320	Plant issue fee	
1460	130	2460	130	Petitions to the Commissioner	
1807	50	1807	50	Processing fee under 37 CFR 1.17(q)	
1806	180	1806	180	Submission of Information Disclosure Stmt	
8021	40	8021	40	Recording each patent assignment per property (times number of properties)	
1809	770	1809	385	Filing a submission after final rejection (37 CFR § 1.129(a))	
1810	770	2810	385	For each additional invention to be examined (37 CFR § 1.129(b))	
1801	770	2801	385	Request for Continued Examination (RCE)	
1802	900	1802	900	Request for expedited examination of a design application	
Other fee (specify)					

* Reduced by Basic Filing Fee Paid

SUBTOTAL (3)

SUBMITTED BY

Complete (if applicable)

Name (Print/Type) Eric S. Hyman

Registration No.
(Attorney/Agent)

30,139

Telephone

(310) 207-3800

Signature

Date

8/10/09



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In Re the Application of:

TAE WOONG KANG, ET AL.

Application No.: 10/691,852

Filed: October 22, 2003

For: single electron device, method of manufacturing the same, and method of simultaneously manufacturing single electron device and mos transistor

Art Group:

Examiner:

INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. §1.97

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

In accordance with the duty of disclosure, enclosed is a copy of IDS Citation Form PTO/SB/08 or PTO-1449, together with copies of the documents cited on that form, except for copies not required to be submitted (e.g., copies of U.S. patents and U.S. published patent applications need not be enclosed for applications filed after June 30, 2003). This IDS and IDS Citation Form are being submitted before the mailing of a first Office Action. It is respectfully requested that the cited references be considered and that the enclosed copy of PTO/SB/08 be initialed by the Examiner to indicate such consideration and a copy thereof returned to applicant(s).

The references were cited in a Search Report dated June 29, 2004 (copy enclosed herewith) in a counterpart Korean application, which was forwarded to Applicant's Representative in a communication dated June 30, 2004.

The submission of this Information Disclosure Statement is not to be construed as a representation that a search has been made in the subject application and is not to be construed as an admission that the information cited in this statement is material to patentability.

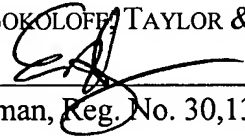
Please charge any fees due to Deposit Account 02-2666. A duplicate copy of the Fee Transmittal (PTO/SB/17) is enclosed for this purpose.

Respectfully submitted,

BLAKELY, SOKOLOFF, TAYLOR & ZAFMAN LLP

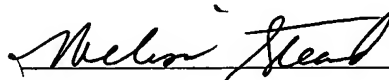
Date: _____

8/10/04


Eric S. Hyman, Reg. No. 30,139

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Melissa Stead

8-11-04

Date

출력 일자: 2004/6/30

발송번호 : 9-5-2004-025847422
발송일자 : 2004.06.29
제출기일 : 2004.08.29

수신 : 서울 중구 순화동 1-170 에이스타워 4층
신영무 귀하

100-712

특허청 의견제출통지서

출원인 명칭 한국전자통신연구원 (출원인코드: 319980077638)
주소 대전 유성구 가정동 161번지

대리인 성명 신영무
주소 서울 중구 순화동 1-170 에이스타워 4층

출원번호 10-2002-0078445

발명의 명칭 단전자 소자, 그 제조 방법 및 단전자 소자와 MOS 트랜지스터를 동
시에 형성하는 제조방법

이 출원에 대한 심사결과 아래와 같은 거절이유가 있어 특허법 제63조의 규정에 의하여 이를 통지하
오니 의견이 있거나 보정이 필요할 경우에는 상기 제출기일까지 의견서[특허법시행규칙 별지 제25호
의2서식] 또는/및 보정서[특허법시행규칙 별지 제5호서식]를 제출하여 주시기 바랍니다.(상기 제출
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지는 하지 않습니다.)

[이유]

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지식을 가진 자가 아래에 지적한 것에 의하여 용이하게 발명할 수 있는 것이므로 특허법 제29조제2
항의 규정에 의하여 특허를 받을 수 없습니다.
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한 것을 특징으로 하는 단전자소자이나, 인용문헌(한국공개특허공보 2002-38274호(2002.05.23))에는
반구형의 나노크리스탈라인 실리콘이 형성된 구성이 실시되어 있었으므로, 본원의 청구범위 전항
에 기재된 발명은 상기 기술분야에서 통상의 지식을 가진 자가 인용문헌에 기재된 발명에 의하여 용
이하게 발명할 수 있습니다.

[첨부]

첨부1 한국공개특허공보 2002-38274호(2002.05.23) 1부. 끝.

2004.06.29

특허청

전기전자심사국

응용소자심사담당관실 심사관 전범재

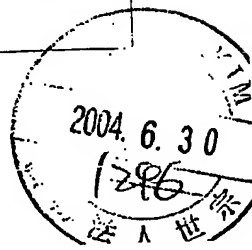


<<안내>>

문의사항이 있으시면 ☎ 042)481-5740 로 문의하시기 바랍니다.

특허청 직원 모두는 깨끗한 특허행정의 구현을 위하여 최선을 다하고 있습니다. 만일 업무처리과정에서 직원의 부조리행위
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▶ 홈페이지(www.kipo.go.kr)내 부조리신고센터



Substitute for form 1449A/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Sheet

of

Complete if Known

Application Number	10/691,852
Filing Date	October 22, 2003
First Named Inventor	Tae Woong Kang
Art Unit	
Examiner Name	
Attorney Docket Number	5882P061

U.S. PATENT DOCUMENTS

[illegible]

FOREIGN PATENT DOCUMENTS

[illegible]

**Examiner
Signature**

Date	
Considered	

*Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication.

¹ Applicant's unique citation designation number (optional). ² See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

Based on PTO/SB/08A (08-03) as modified by Blakely, Solokoff, Taylor & Zafman (wlr) 08/11/2003.

Send To: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450

KOREAN PATENT ABSTRACTS

(11)Publication number: 1020020038274 A
(43)Date of publication of application: 23.05.2002

(21)Application number: 1020000068406

(22)Date of filing: 17.11.2000

(51)Int. Cl. H01L 27/10

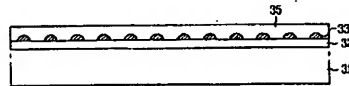
(71)Applicant: HYNIX SEMICONDUCTOR INC.

(72)Inventor: KIM, IL GWON

(54) METHOD FOR FORMING SILICON QUANTUM DOT AND METHOD FOR FABRICATING NON-VOLATILE MEMORY DEVICE USING THE SAME

(57) Abstract:

PURPOSE: A method for forming a silicon quantum dot is provided to form a high density silicon quantum dot, by forming an insulation layer by a vapor deposition method after amorphous silicon is seeded and by performing an oxidation process after the amorphous silicon is polished through a chemical mechanical polishing(CMP) process.



CONSTITUTION: The first insulation layer is formed on a semiconductor substrate(31). A plurality of nano-crystalline silicon(33) are formed on the first insulation layer. The second insulation layer is formed on the first insulation layer including the nano-crystalline silicon. A part of the second insulation layer and the nano-crystalline silicon is etched. The surface of the nano-crystalline silicon is oxidized.

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Legal Status

Date of request for an examination (20001117)

Final disposal of an application (registration)

Date of final disposal of an application (20030428)

Patent registration number (1003866140000)

Date of registration (20030523)